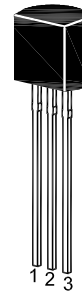


ST 2SA1206

PNP Silicon Epitaxial Planar Transistor

for general purpose amplifier and high speed switching applications.

On special request, these transistors can be manufactured in different pin configurations.



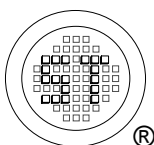
1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	15	V
Collector Emitter Voltage	$-V_{CEO}$	15	V
Emitter Base Voltage	$-V_{EBO}$	4.5	V
Collector Current	$-I_C$	50	mA
Collector Pulse Current ($PW \leq 2\text{ ms}$)	$-I_{CP}$	100	mA
Power Dissipation	P_{tot}	600	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 10\text{ mA}$ at $-V_{CE} = 1\text{ V}$, $-I_C = 1\text{ mA}$	h_{FE} h_{FE}	50 30	150 -	- -
Collector Base Cutoff Current at $-V_{CB} = 8\text{ V}$	$-I_{CBO}$	-	0.1	μA
Emitter Base Cutoff Current at $-V_{EB} = 3\text{ V}$	$-I_{EBO}$	-	0.1	μA
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$	$-V_{CE(sat)}$	-	0.2	V
Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$	$-V_{BE(sat)}$	-	0.95	V
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $I_E = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	800	-	MHz
Output Capacitance at $-V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	3	pF



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